

JMT2302AN

20V, 4A⁽¹⁾, N-channel MOSFET

Physical Characteristics

	<p>Die size: 624µm x 583µm (including scribe line) Gate: 138µm x 138µm Gross die / per 8" wafer =81500pcs</p> <p>For SOT-23 package Suggest Bonding wire: Gate: 1*42um Cu Source: 5*42um Cu</p>	
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Mechanical Data

Nominal Back Metal Composition, Thickness:	Ti- Ni - Ag, (1kA°-2kA°-10kA°)
Nominal Front Metal Composition, Thickness:	AlCu(4um)
Wafer Diameter:	200mm, with 010 notch
Wafer Thickness:	160µm
Scribe line width	60µm
Passivation	SiN

Electrical Characteristics after SOT-23 package (T_J=25°C)

Parameter	Description	Min.	Typ.	Max.	Unit	Test Condition
V _{(BR)DSS}	Drain-Source Breakdown Voltage	20	—	—	V	V _{GS} =0V, I _D =250µA
R _{DS(ON)}	Static Drain-Source On-Resistance	—	23	30	mΩ	V _{GS} =4.5V, I _D =4A ⁽¹⁾
		—	32	45	mΩ	V _{GS} =2.5V, I _D =3A ⁽¹⁾
V _{GS(th)}	Gate Threshold Voltage	0.5	0.7	1	V	V _{DS} = V _{GS} , I _D =250µA
I _{DSS}	Drain-to-Source Leakage Current	—	—	1	µA	V _{DS} = 20V, V _{GS} = 0V
I _{GSS}	Gate-Body Leakage Current	—	—	±100	nA	V _{DS} = 0V, V _{GS} = ±12V
T _J , T _{STG}	Operating and Storage Temperature	-55°C to 150°C Max				

Note:

(1) This characteristics assumes the die are assembled in SOT-23 packages. Actual performance may degrade when assembled. JieJie does not guarantee device performance after assembly.




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